

Attorney Docket # 5367-90

Express Mail #EV410260275US
Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Christine HOESS et al.

Serial No.: n/a

Filed: concurrently

For: Method for Fabricating at least one Mesa or
Ridge Structure or at least one Electrically
Pumped Region in a Layer or Layer
Sequence

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

S I R:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO/SB/08A. Copies of the listed documents are also enclosed.

In accordance with 37 C.F.R §§1.97(g) and (h), the filing of this Information Disclosure Statement should not be construed as a representation that a search has been made or that information cited is, or is considered to be, material to patentability as defined in §1.56(b), or that any cited document listed or attached is (or constitutes) prior art. Unless otherwise indicated, the date of publication indicated for an item is taken from the face of the item and Applicant(s) reserve(s) the right to prove that the date of publication is in fact different.

If any fees or charges are deemed required at this time in connection with the application, the same may be charged to our Patent and Trademark Office Deposit Account No. 03-2412.

It is respectfully requested that the above information be considered by the Examiner and that the copy of the enclosed Form PTO SB/08A be returned indicating that such information has been considered.

Respectfully submitted,
COHEN, PONTANI, LIEBERMAN & PAVANE

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Dated: March 19, 2004

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Substitute for Form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	
		Filing Date	
		First Named Inventor	Christine HOESS
		Art Unit	
		Examiner Name	
Sheet 1 of 2	Attorney Docket Number		5367-90

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind-Code ² (if known)			
		US-6,661,822 B1	12/09/2003	Kubota et al.	
		US-5,426,658	06/20/1995	Kaneno et al.	
		US-4,949,352	08/14/1990	Plumb	
		US-4,751,708	06/14/1998	Jackson et al.	
		US-4,296,386	10/20/1981	Tijburg et al.	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind-Code ⁵ (if known)				
		JP 2001-015860	01/19/2001	Fujitsu Ltd.		✓
		DE 101 47 791 A1	09/27/2001	Osram Opto Semiconductors GmbH		

Examiner Signature		Date Considered	
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		Filing Date	
		First Named Inventor	Christine HOESS
		Art Unit	
		Examiner Name	
Sheet 2 of 2	Attorney Docket Number	5367-90	
NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Tsuyoshi Tojyo, et al., "High-Power AlGaInN Laser Diodes with High Kink Level and Low Relative Intensity Noise", Jpn. J. Appl. Phys. Vol. 41, pp. 1829-1833, March 2002	
		Shin-ya Nunoue et al., "Reactive Ion Beam Etching and Overgrowth Process in the Fabrication of InGaN Inner Stripe Laser Diodes", Jpn. J. Appl. Phys. Vol. 37, pp. 1470-1473, March 1998	
		M. Kuramoto et al., "Reduction of Internal Loss and Threshold Current in a Laser Diode with a Ridge by Selective Re-Growth (RiS-LD)", phys.stat.sol.(a) 192, No. 2, pp. 329-334 (2002)	
		Masaru Kuramoto et al., "Novel-Ridge InGaN Multiple-Quantum-Well Laser Diodes Fabricated by Selective Area Re-Growth on n-GaN Substrates", Jpn. J. Appl. Phys. Vol. 40, pp. L925-L927, 15 Sept. 2001	
		Akitaka Kimura et al., "Composition Control during Growth of AlGaIn Cladding Layers for InGaIn-MQW Lasers with Ridge Formed by Selective Re-growth (RiS-type Lasers)", Mat. Res. Soc. Symp. Proc. Vol. 693, Materials Research Society, pp. 14.5.1-14.5.6 (2002)	
		Bulman G., et al. "InGaIn/GaN laser diodes grown on 6H-SiC", pp. 616-622, August 1998	
Examiner Signature	Date Considered		

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